

# **Dual N-Channel Power MOSFET**

20V, 6.0A, 30mΩ

#### **FEATURES**

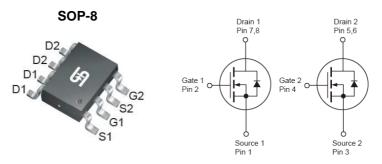
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
$V_{DS}$		20	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = 4.5V$	30		
	$V_{GS} = 2.5V$	40	mΩ	
$Q_g$		4.86	nC	

#### **APPLICATION**

- Specially Designed for Li-on Battery Packs
- Battery Switch Application





Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	±12	V
Continuous Drain Current (Note 1)	$T_C = 25$ °C	I <sub>D</sub>	6	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	30	А
Continuous Source Current (Diode Conduction)		Is	1.7	А
Total Power Dissipation	T <sub>A</sub> = 25°C	ם	1.6	10/
	$T_A = 75$ °C	P <sub>DTOT</sub>	1.1	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	40	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	77	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)	1					•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	0.6			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			А
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6.0A$			21	30	mΩ
	$V_{GS} = 2.5V, I_D = 5.2A$	R <sub>DS(ON)</sub>		30	40	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g <sub>fs</sub>		30		S
Dynamic (Note 4)						
Total Gate Charge		Qg		4.86		
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	$Q_{gs}$		0.92		nC
Gate-Drain Charge		$Q_{gd}$		1.4		]
Input Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$ - F = 1.0MHz	C <sub>iss</sub>		562		
Output Capacitance		C <sub>oss</sub>		106		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		75		
Switching (Note 5)						
Turn-On Delay Time	$V_{DD} = 10V,$ $R_{GEN} = 6\Omega,$ $I_{D} = 1A, V_{GS} = 4.5V,$	t <sub>d(on)</sub>		8.1		
Turn-On Rise Time		t <sub>r</sub>		9.95		]
Turn-Off Delay Time		t <sub>d(off)</sub>		21.85		ns
Turn-Off Fall Time		t <sub>f</sub>		5.35		
Source-Drain Diode (Note 3)						
Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	$V_{SD}$		0.7	1.2	V

### Notes:

- 1. Pulse width limited by the Maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 5$  sec.
- 3. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.



## **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM9926DCS RLG	SOP-8	2,500pcs / 13" Reel

#### Note:

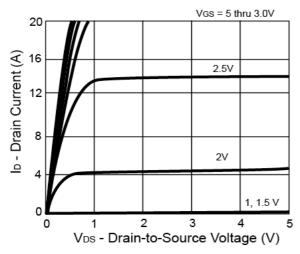
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



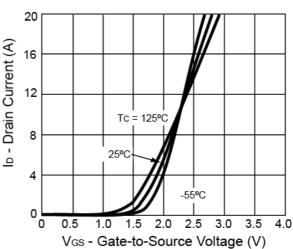
### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

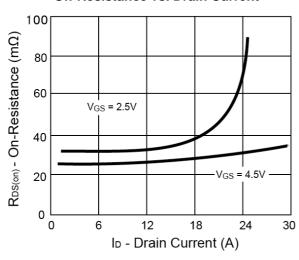
# **Output Characteristics**



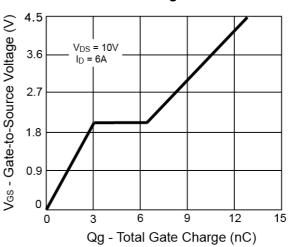
**Transfer Characteristics** 



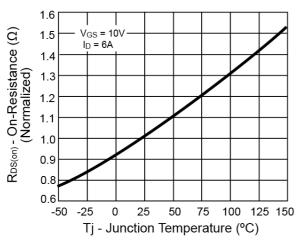
**On-Resistance vs. Drain Current** 



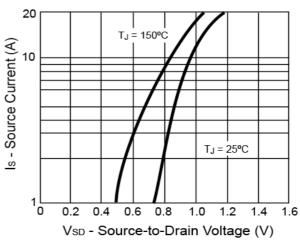
**Gate Charge** 



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

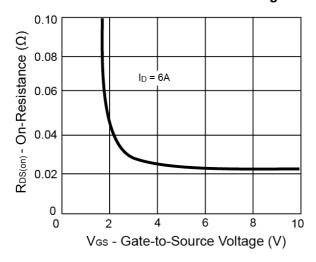


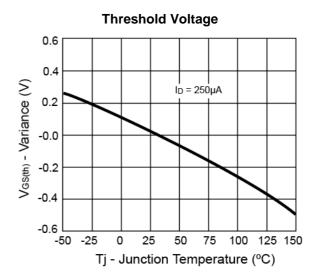


### **CHARACTERISTICS CURVES**

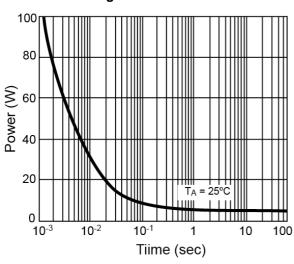
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

### On-Resistance vs. Gate-Source Voltage

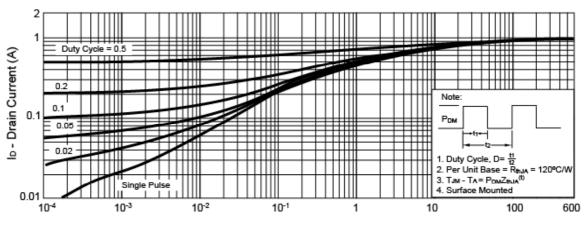




### Single Pulse Power



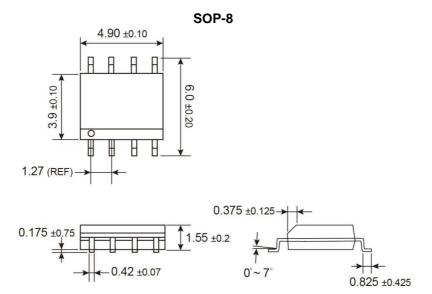
# Normalized Thermal Transient Impedance, Junction-to-Ambient



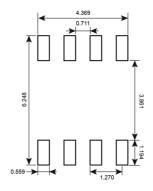
Square Wave Pulse Duration (sec)



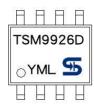
# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



## SUGGESTED PAD LAYOUT (Unit: Millimeters)



### **MARKING DIAGRAM**



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code (1~9, A~Z)





### **Notice**

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.